

Session Program

11-13 Jun 2014

24th RD50 Workshop (Bucharest)

***Session 1 - Defect and Material
Characterization***

Bucharest

Wednesday 11 June

09:00

Session 1 - Defect and Material Characterization

Session | **Location:** Bucharest | **Convener:** Dr Ioana Pintilie

09:00–09:05 Workshop opening

Speaker

Dr Ionut Enculescu

09:05–09:10 Workshop opening

Speakers

Dr Ioana Pintilie, Michael Moll

09:10–09:30

Investigation of point and extended defects in electron irradiated silicon - dependence on the particle energy

Speaker

Roxana Radu

09:30–09:50

Effect of background impurities and electronic excitation on the behavior of radiation induced interstitial boron complexes

Speaker

Leonid Makarenko

09:50–10:10

A_{Si}-Si_i defect as possible origin of electronically activated degradation of boron and indium doped silicon

Speaker

Dr Kevin Lauer

10:10–10:30

Electron Induced Damage in Silicon - TRIM and TCAS Simulations

Speaker

Prof. Gunnar Lindstroem

10:30–11:00

Coffee

11:00–11:20

Modelling Vacancy-Interstitial Clusters and their effect on on Carrier Transport in Silicon

Speaker

Dr Ernestas Zsinas

11:20–11:40

ESR investigation of paramagnetic point defects in O doped crystalline Si-FZ irradiated with 27 MeV electrons

Speaker

S.V. Nistor

11:40-12:00

High resolution transmission electron microscopy (HRTEM) investigations of silicon irradiated with high energy electrons

Speaker

Leona Nistor

12:00-12:30

Discussion: Defect and Material Characterization

Speaker

Dr Ioana Pintilie

13:00